

TECHNICAL DATA  
DATA SHEET 4749, REV. C**SILICON SCHOTTKY RECTIFIER**  
**Ultra Low Reverse Leakage**  
**175°C Operating Temperature****Applications:**

- Switching Power Supply
- Converters
- Free-Wheeling Diodes
- Polarity Protection Diode

**Features:**

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

**Maximum Ratings:**

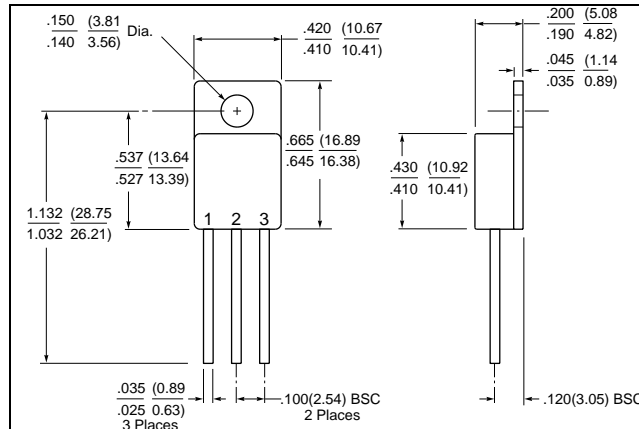
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	3.0	A
Max. Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine wave	55	A
Max. Junction Temperature	$T_J$	-	-65 to +175	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +175	°C
Thermal Resistance (per leg)	$R_{\theta JC}$	-	11.9	°C/W

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 3A, Pulse, $T_J = 25\text{ °C}$	0.94	V
	$V_{F2}$	@ 3A, Pulse, $T_J = 125\text{ °C}$	0.78	V
Max. Reverse Current	$I_{R1}$	@ $V_R = 100V$ , Pulse, $T_J = 25\text{ °C}$	0.025	mA
	$I_{R2}$	@ $V_R = 100V$ , Pulse, $T_J = 125\text{ °C}$	0.25	mA
Max. Junction Capacitance	$C_T$	@ $V_R = 5V$ , $T_C = 25\text{ °C}$ $f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)	100	pF

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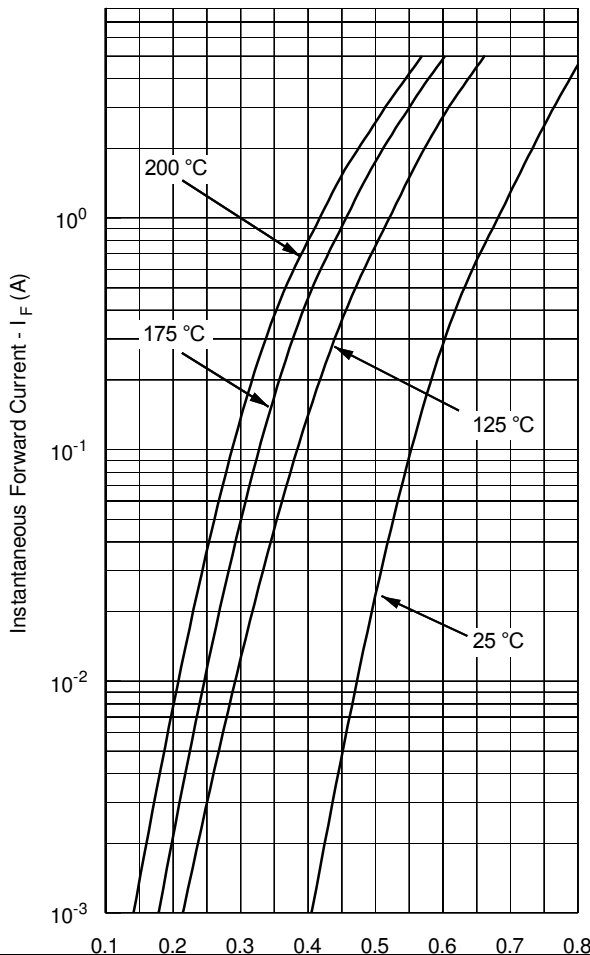
Mechanical Dimensions: In Inches / mm



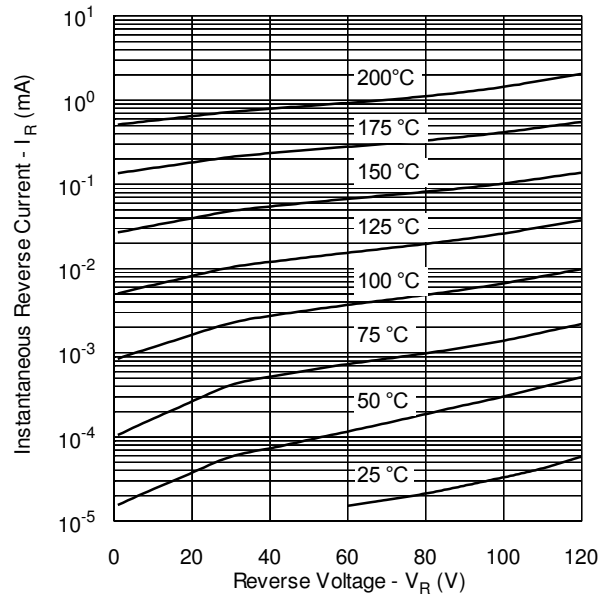
**TO-257**

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

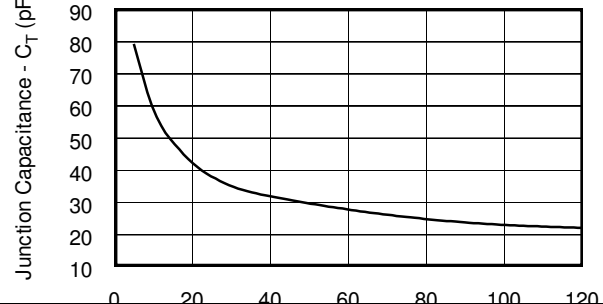
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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